

ABSTRACT OF THE DISCLOSURE

A semiconductor device is provided in which the difference in characteristics between a pair of sense amplifier transistors of a DRAM is suppressed, whereby the sensitivity of a sense amplifier is enhanced. A pair
5 of gate electrodes of a N-type sense amplifier transistor and a pair of gate electrodes of a P-type sense amplifier transistor constituting a CMOS sense amplifier of the DRAM respectively are placed in parallel to each other in one active region in the same direction as that of bit lines. A pair of adjacent
10 N-type sense amplifier transistors and a pair of adjacent P-type sense amplifier transistors are isolated by STI.